

# TeraHertz Pulse Modelling

David Newton

david.newton@liverpool.ac.uk

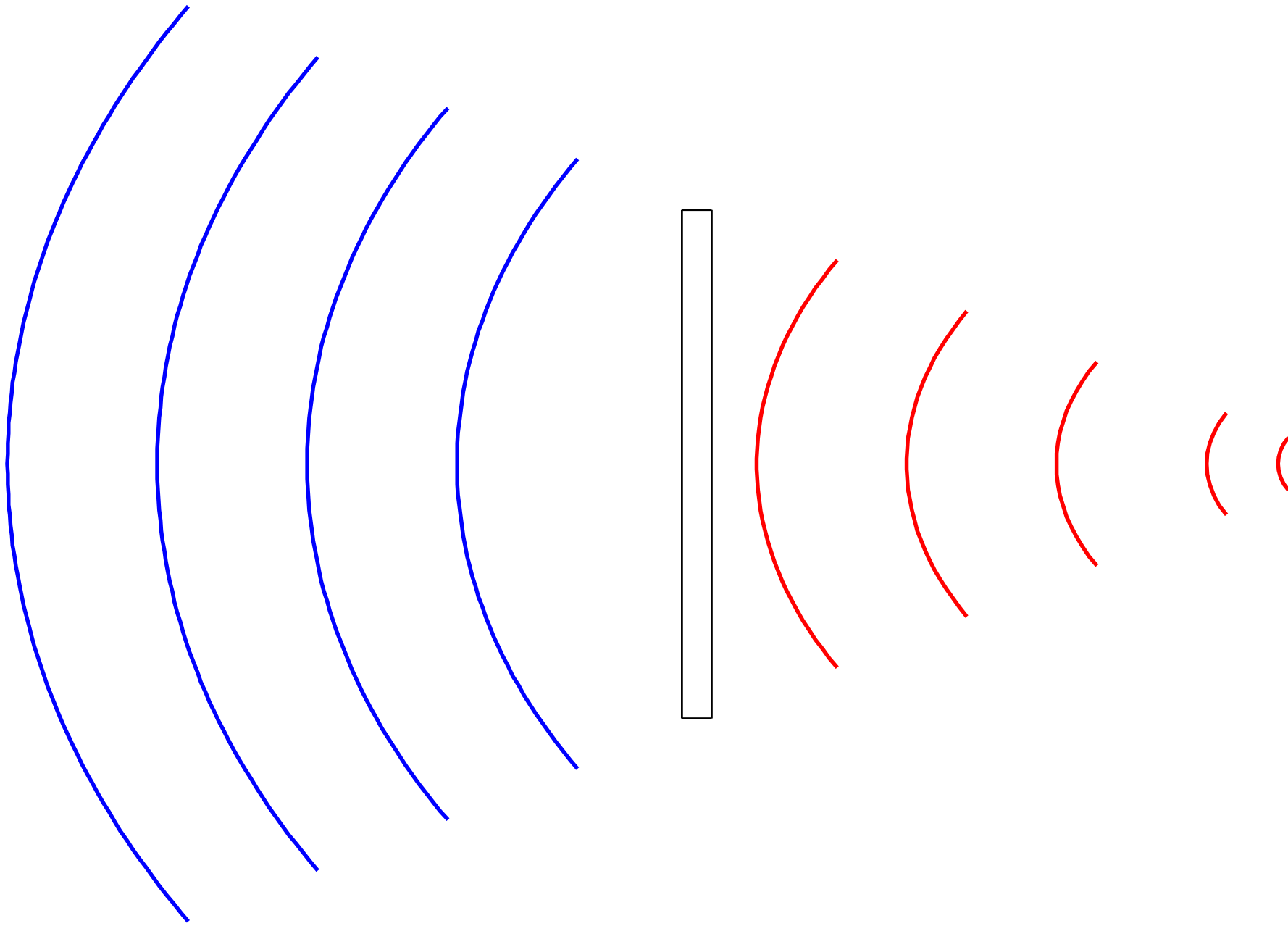
University of Liverpool, Cockcroft Institute

20/10/2010

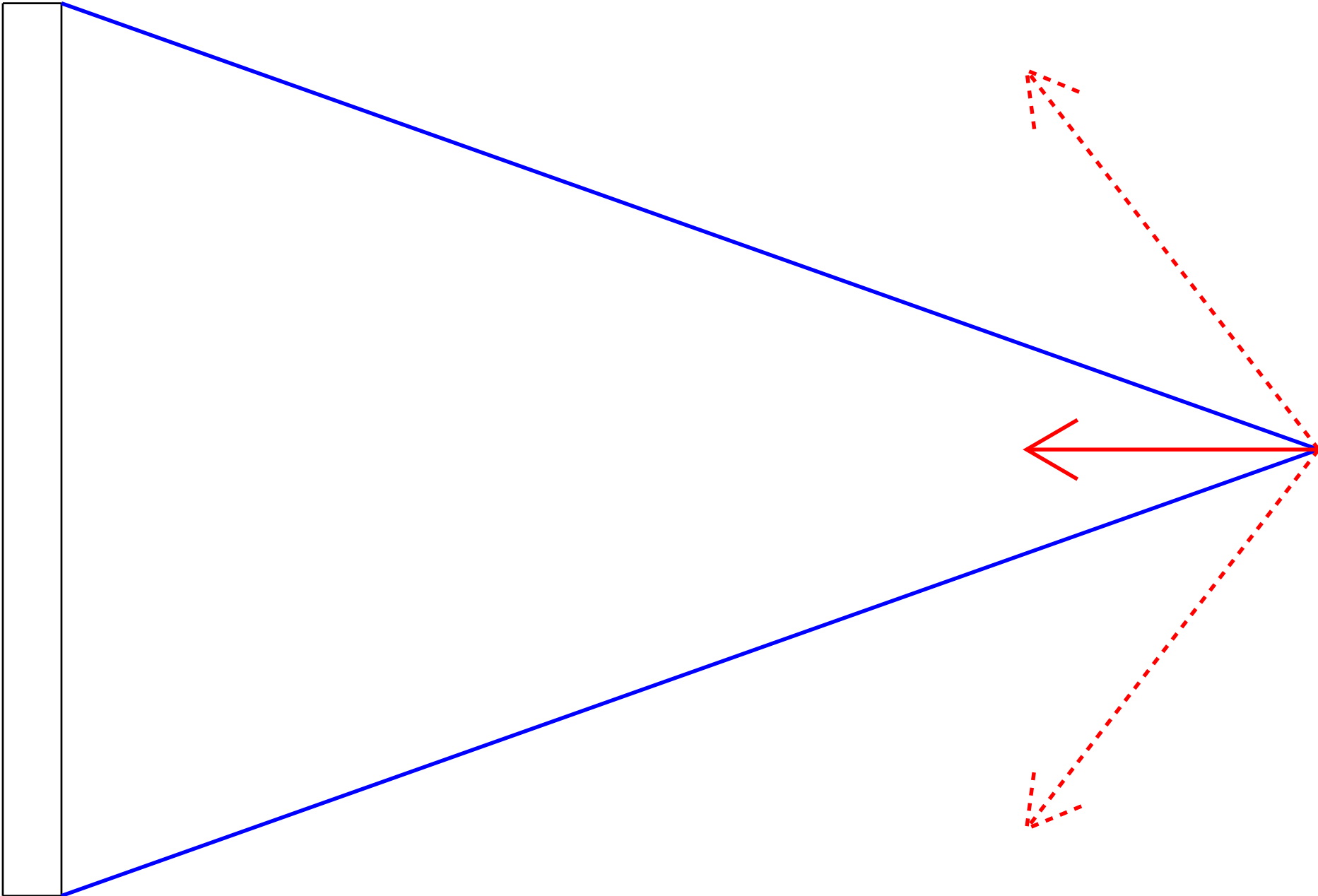
# Project Outline

- **Aim** – to produce evidence of a interaction of an EM wave with a electron beam in free space;
- **By** – using a longitudinally polarised terahertz beam to produce energy modulation in ALICE electron beam;
- **How** - terahertz radiation generated by converting the mid-IR multi- 10 *terawatt* laser into *terahertz* radiation using a semiconductor wafer-based antenna;
- **Observe** - the result of the radiation-electron bunch interaction in a high-dispersion region of ALICE.

# Focusing of the THz Pulse



# Generation of a Longitudinal Electric Field



# Synchrotron Radiation Calculation

Accelerated charges radiate energy.

The observed electric field of the emitted radiation is:

$$\vec{E}(t) = \frac{n_e e}{4\pi\epsilon_0 c} \left( \frac{c(\vec{n} - \vec{\beta})}{\gamma^2 |\vec{R}|^2 (1 - \vec{\beta} \cdot \vec{n})^3} + \frac{\vec{n} \times [(\vec{n} - \vec{\beta}) \times \dot{\vec{\beta}}]}{|\vec{R}| (1 - \vec{\beta} \cdot \vec{n})^3} \right)_{RET}$$

To calculate  $\vec{E}(t)$  we need to know  $n_e$ ,  $v_d$  and  $\dot{v}_d$ .

# Modelling the Surge Current

At the last talk the current was modelled using an expression (after Benicewicz et.al. J. Opt. Soc. Am. B, 11,12 (1994))

$$\vec{J}_s(t) = \frac{\sigma_s(t)\vec{E}_b}{\frac{\sigma(s)(t)\eta_0}{1+n} + 1} = n_e q \vec{v}_d(t)$$

$n$  is the refractive index of the wafer,  $\eta_0$  is the impedance of free space and  $\sigma_s$  is the surface conductivity:

$$\sigma_s = \frac{e(1-R)}{\hbar\omega} \int_{-\infty}^t dt' m I_{opt}(t')$$

where,

$\vec{E}_b$  is the bias voltage

$R$  is the wafer reflectivity

$m$  is the carrier mobility (assumed to be constant, with a lifetime  $\gg$  laser pulse)

# Modelling the Surge Current

A more ‘physical’ description is given by the Drude model:

$$\vec{J}_s(t, t_0) = \frac{n_e q^2 \tau}{m} \vec{E}_b = n_e q \vec{v}_d(t, t_0)$$

$$\vec{v}_d(t, t_0) = \frac{q\tau \vec{E}_b}{m^*} \left( 1 - \exp\left(-\frac{t - t_0}{\tau}\right) \right)$$

$\vec{v}_d(t, t_0)$  is the drift velocity, at time  $t$ , of charge carriers created at time  $t_0$

$\tau$ , is the scattering constant ( assumed to be  $10^{-12} \text{ s}^{-1}$ )

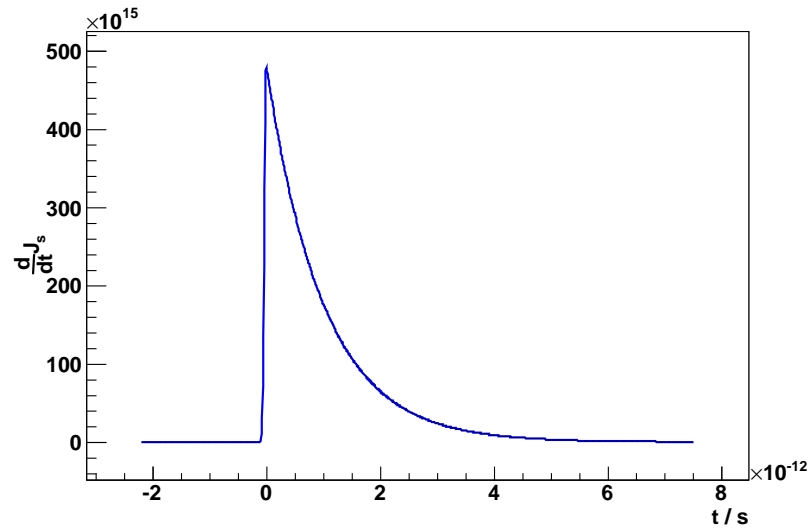
$m^*$  is the effective mass of the carriers.

$n_e q$  is the charge density, which is proportional to the laser intensity.

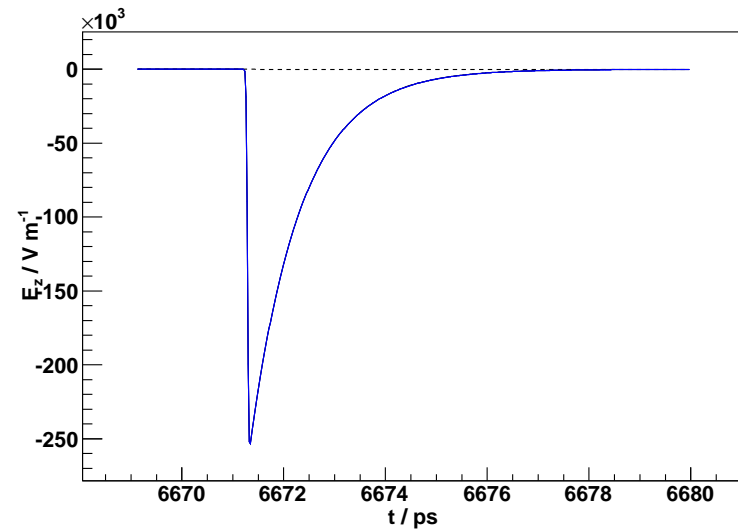
Finally,

$$J_s(t) = \int_{-\infty}^t J_s(t, t_0) dt_0$$

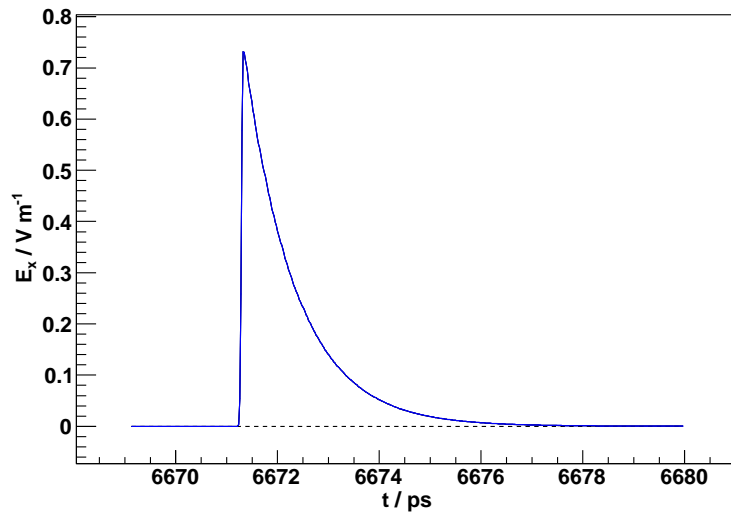
# The Surge Current and the on-axis pulse



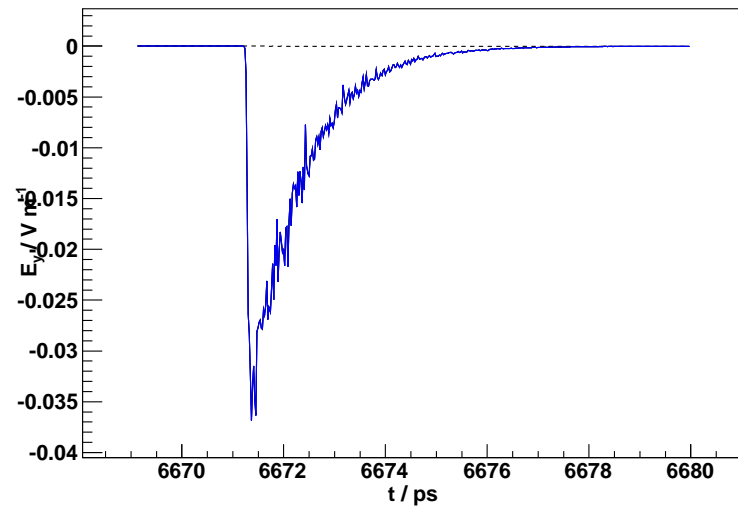
$$\frac{dJ_s}{dt}$$



$$E_z$$



$$E_x$$

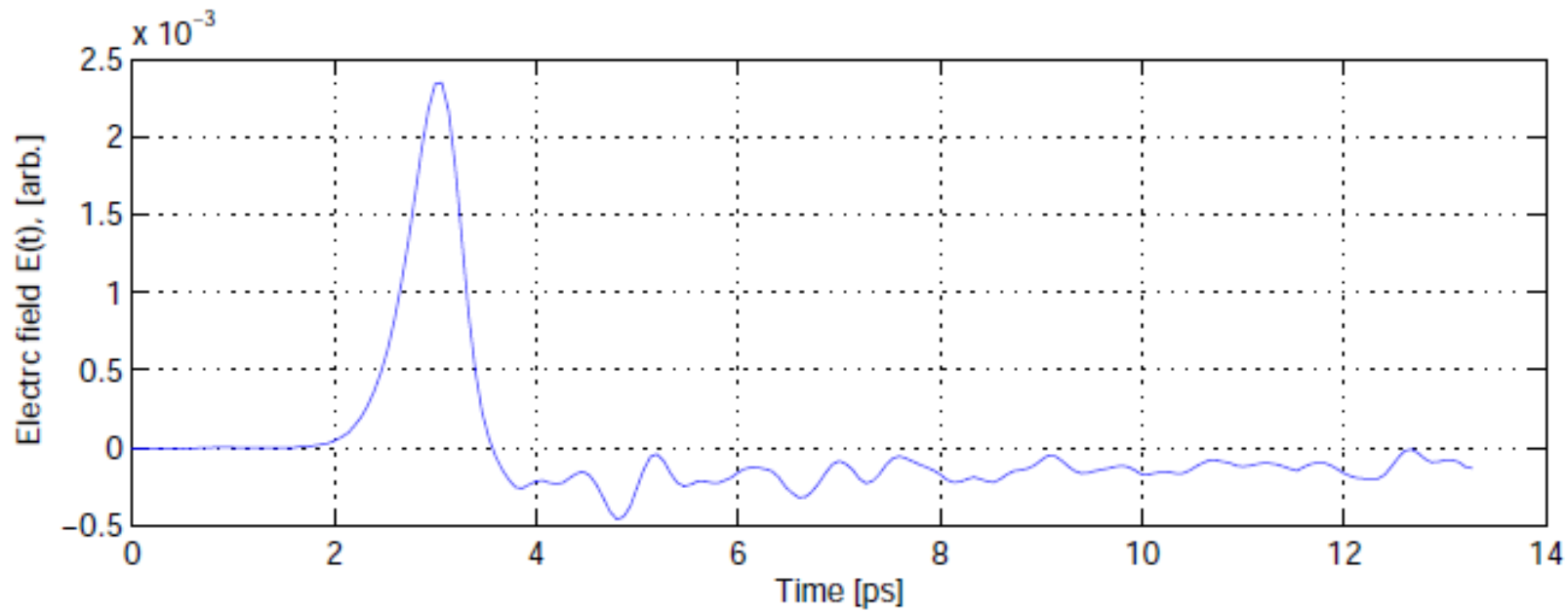


$$E_y$$



# Comparison with Experimental Results

Example pulse from a SQUARE wafer:



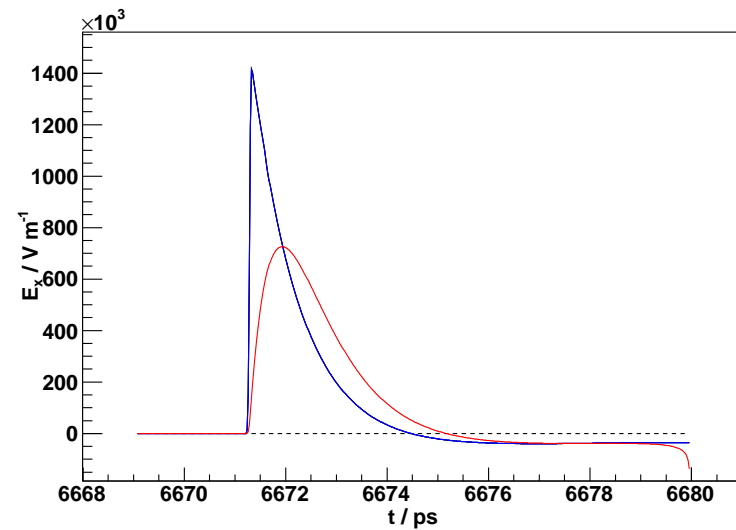
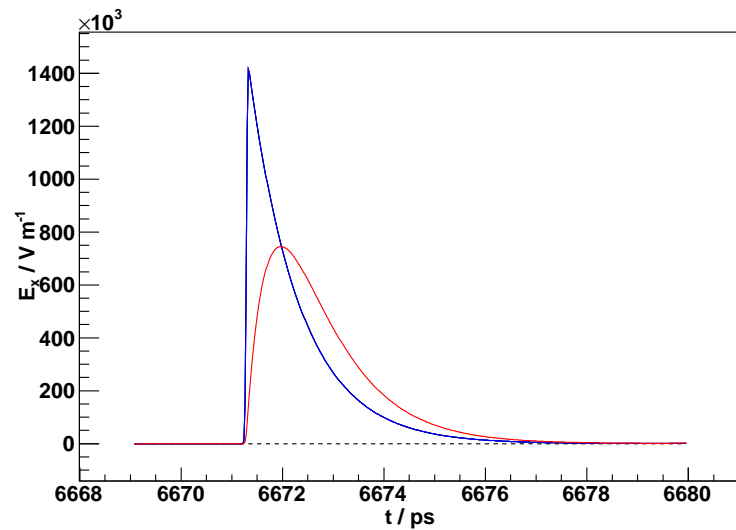
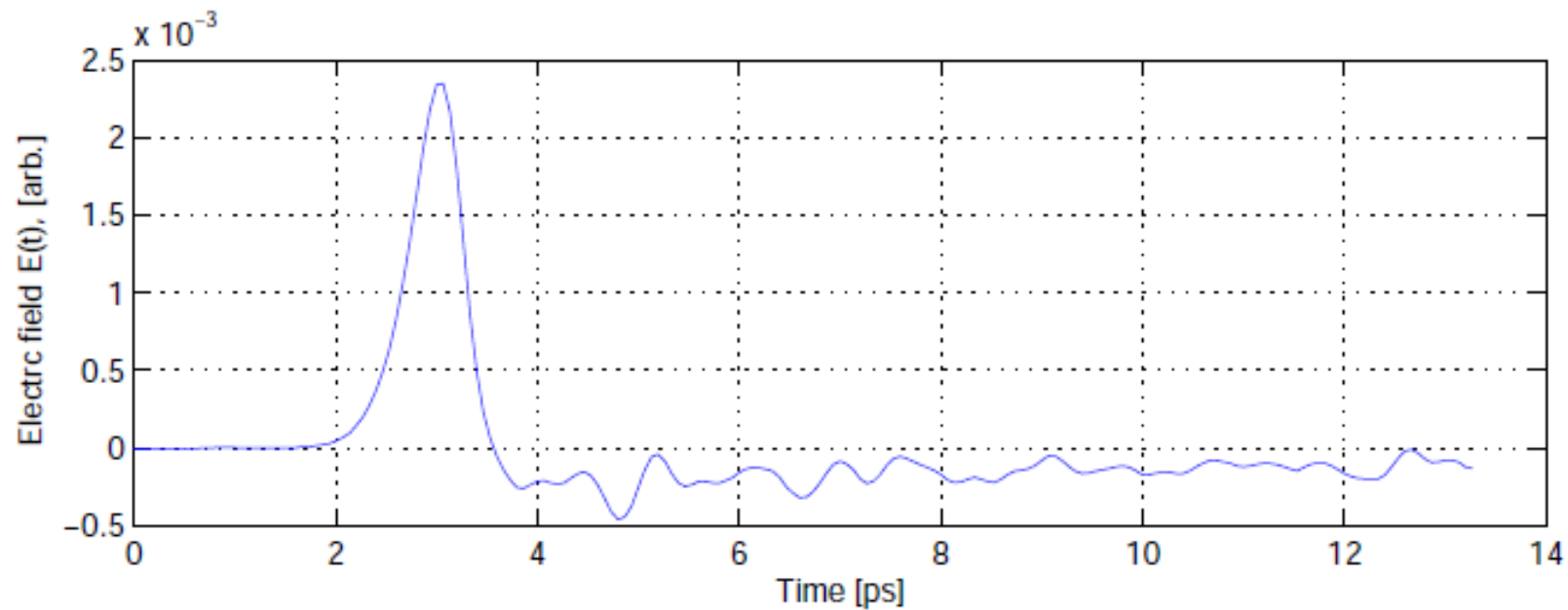
# Model Parameters Square Wafer

- Wafer dimension = 7.5cm
- Bias Voltage = 5,000 V
- Laser Characteristics:
  - Gaussian Profile, FWHM=40 fs
  - Top-Hat transverse profile
  - Energy / Pulse: 1 mJ
- Scattering Rate =  $1.10^{12}$
- electron effective mass =  $0.063 m_e$
- Reflectivity = 0.5

# Square Wafer

$E_x, E_z$  observed at (0.0,0.0,2.0)

(near field:dash, far field: solid, total field: blue, convolved field: red)

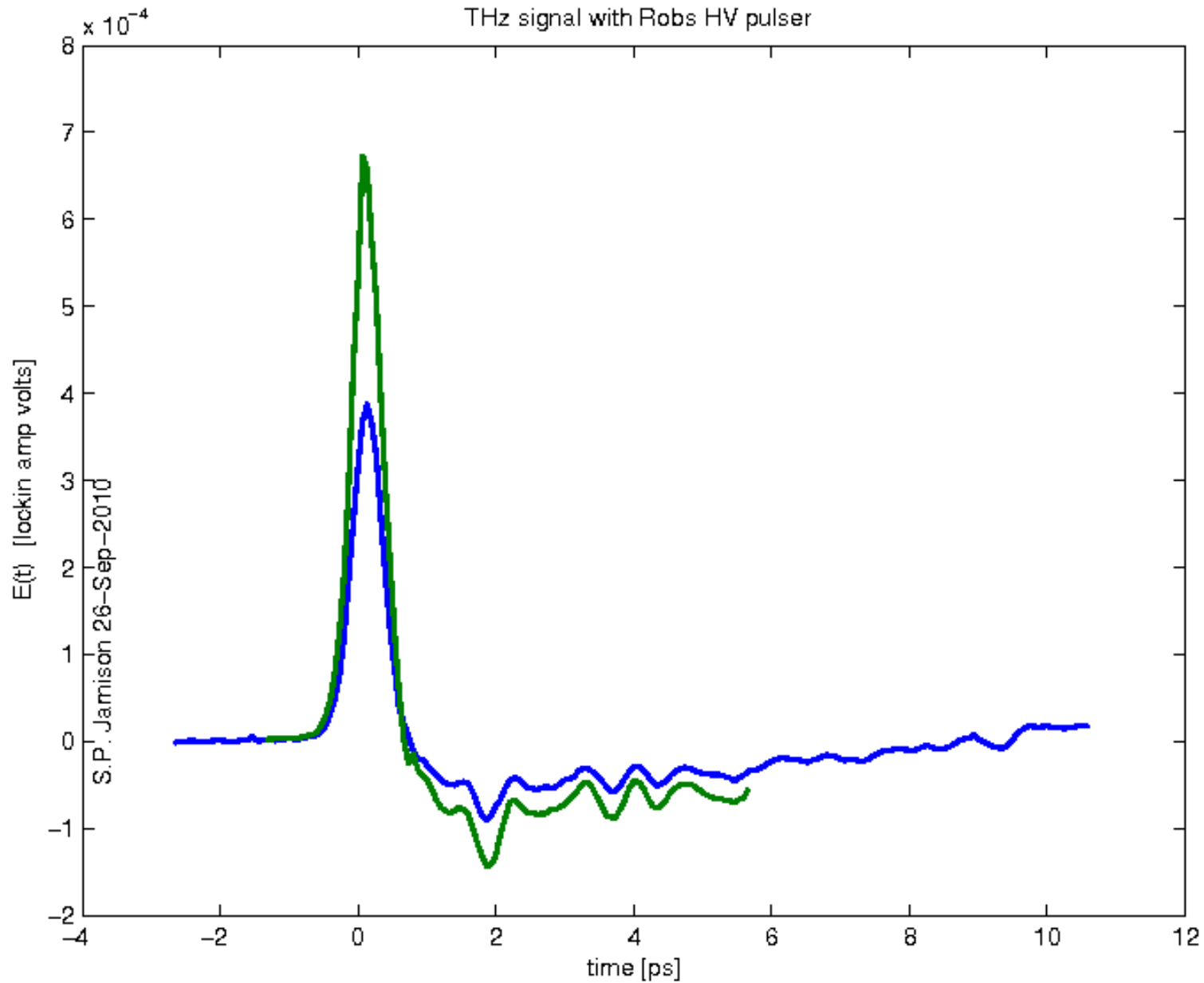


# Model Parameters Round Wafer

- Wafer dimension = 7.5cm
  - Outer electrode: 2.5 mm radius
  - Inner electrode: 10 mm radius
- Bias Voltage = 30,000 V
- Laser Characteristics:
  - Gaussian Profile, FWHM=40 fs
  - Top-Hat transverse profile
  - Energy / Pulse: 1 mJ
- Scattering Rate =  $1.10^{12}$
- electron effective mass =  $0.083 m_e$
- Reflectivity = 0.5
- Laser Focus = 2 m

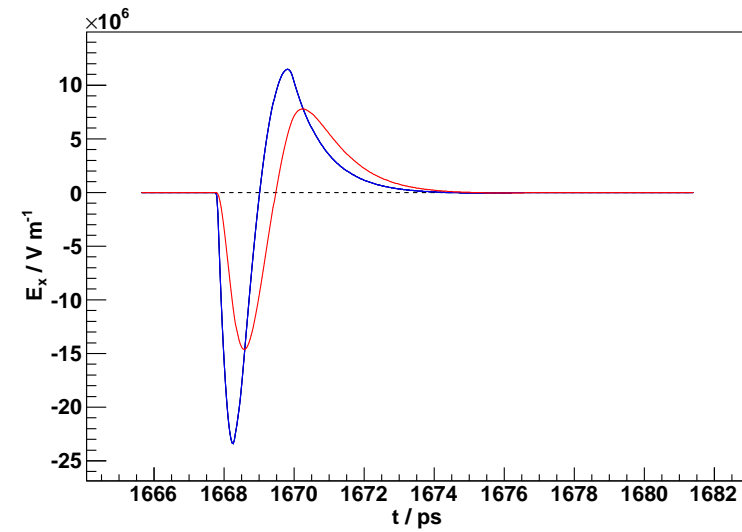
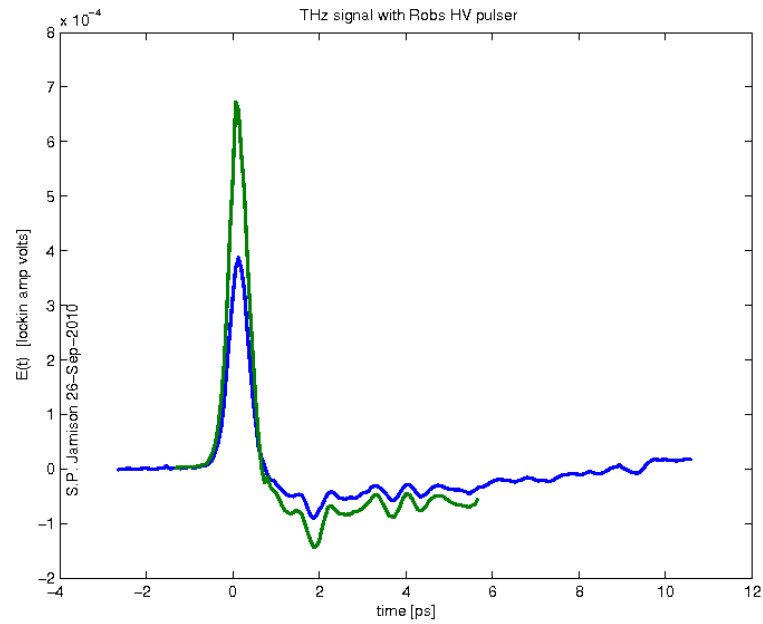
# Round Wafer Experimental Result

The Longitudinal Electric Field (note: arbitrary units)



# Round Wafer off-axis Longitudinal Field

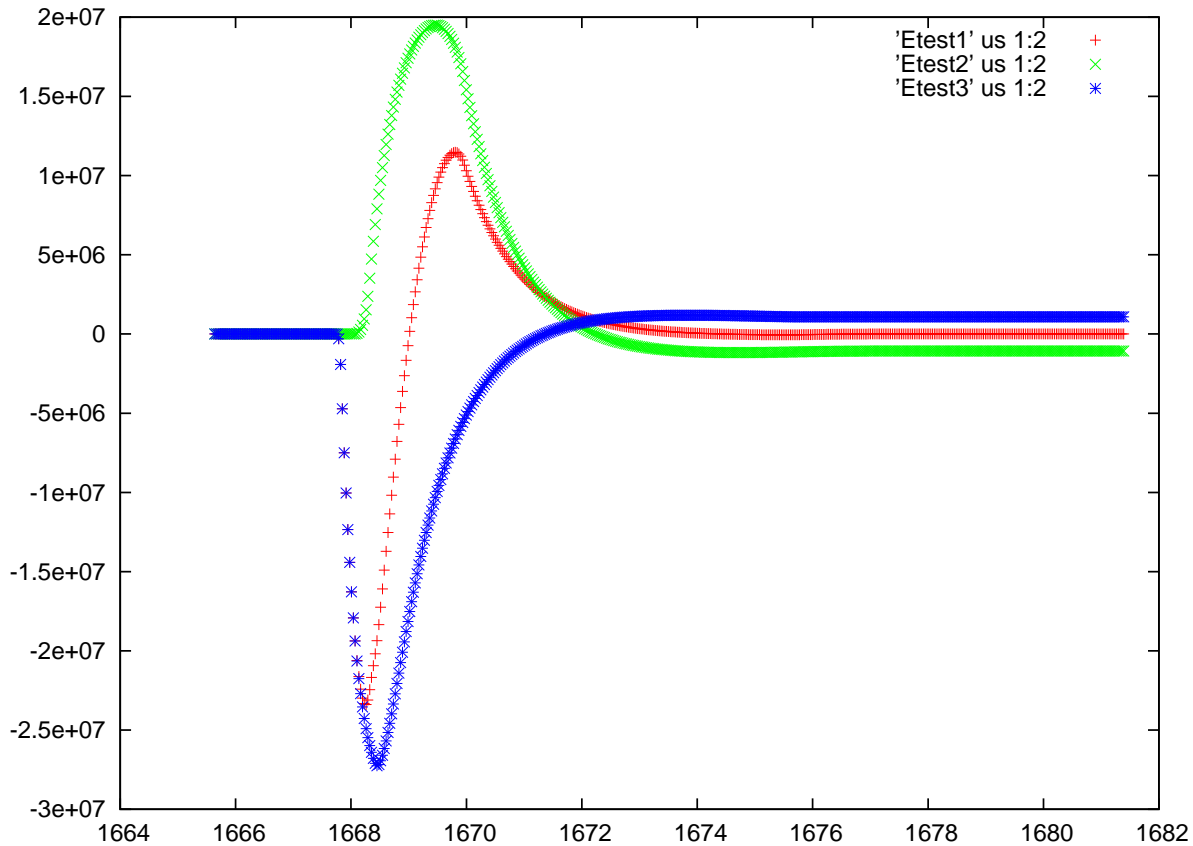
## Experimental vs Simulation



# Round Wafer Simulation

## Off-axis Longitudinal Field

Double pulse is due to symmetry breaking from different section of the wafer



Red points - Total pulse

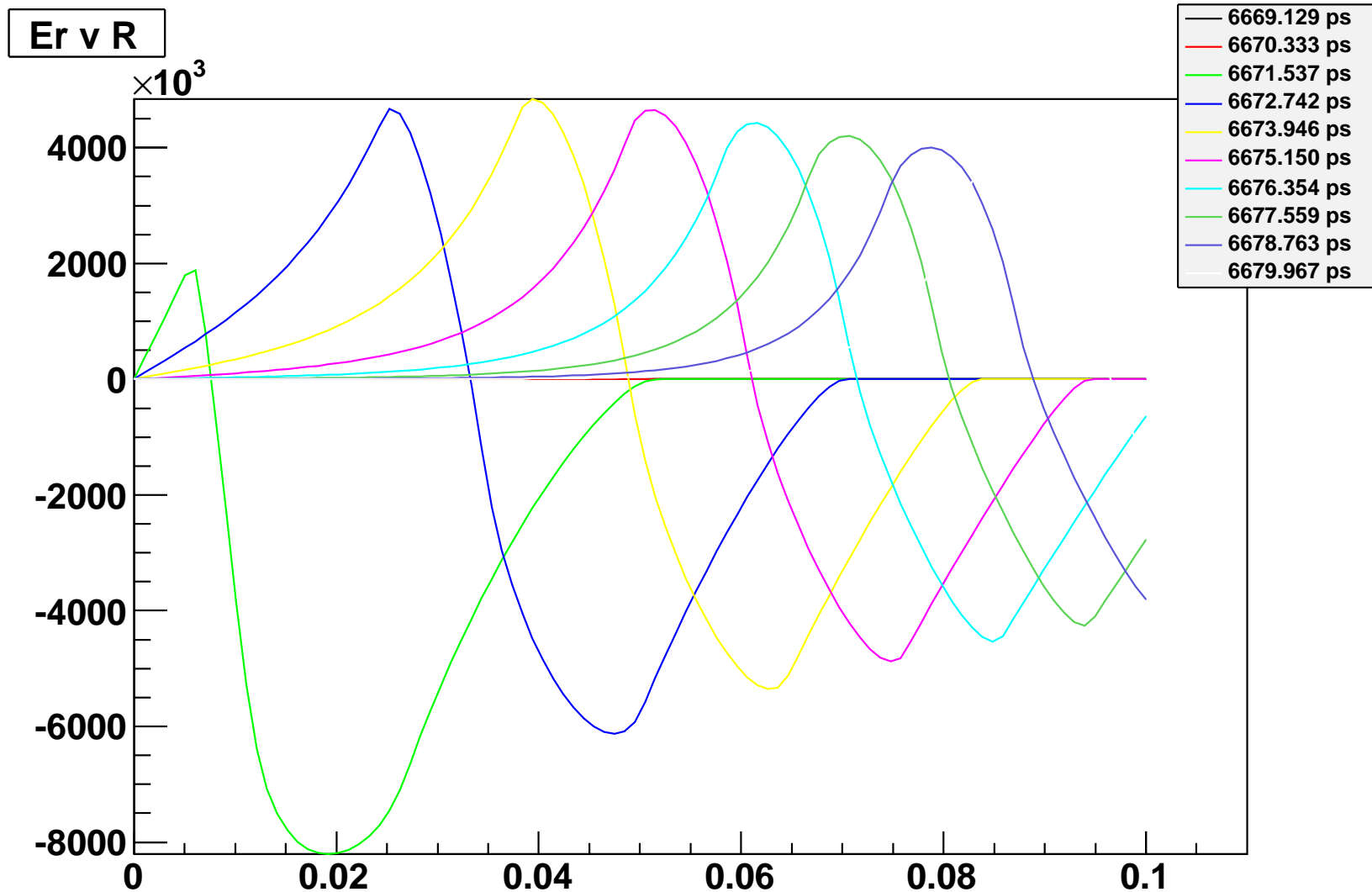
Blue points - pulse from half the wafer

Green points - pulse from the other half of the wafer

nb - No overshoot!

# Round Wafer

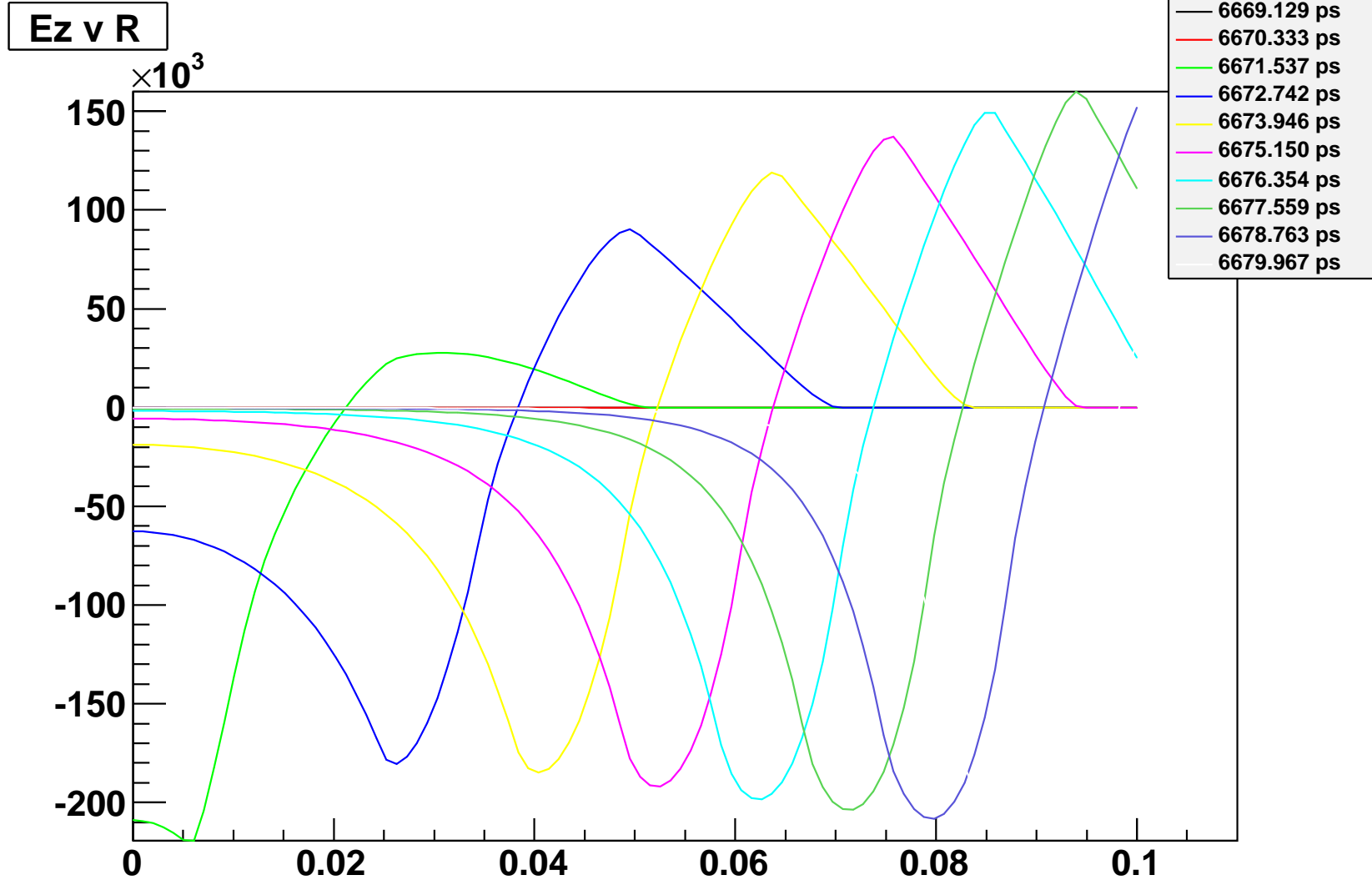
Simulated off-axis radial fields at 2.0 m





# Round Wafer

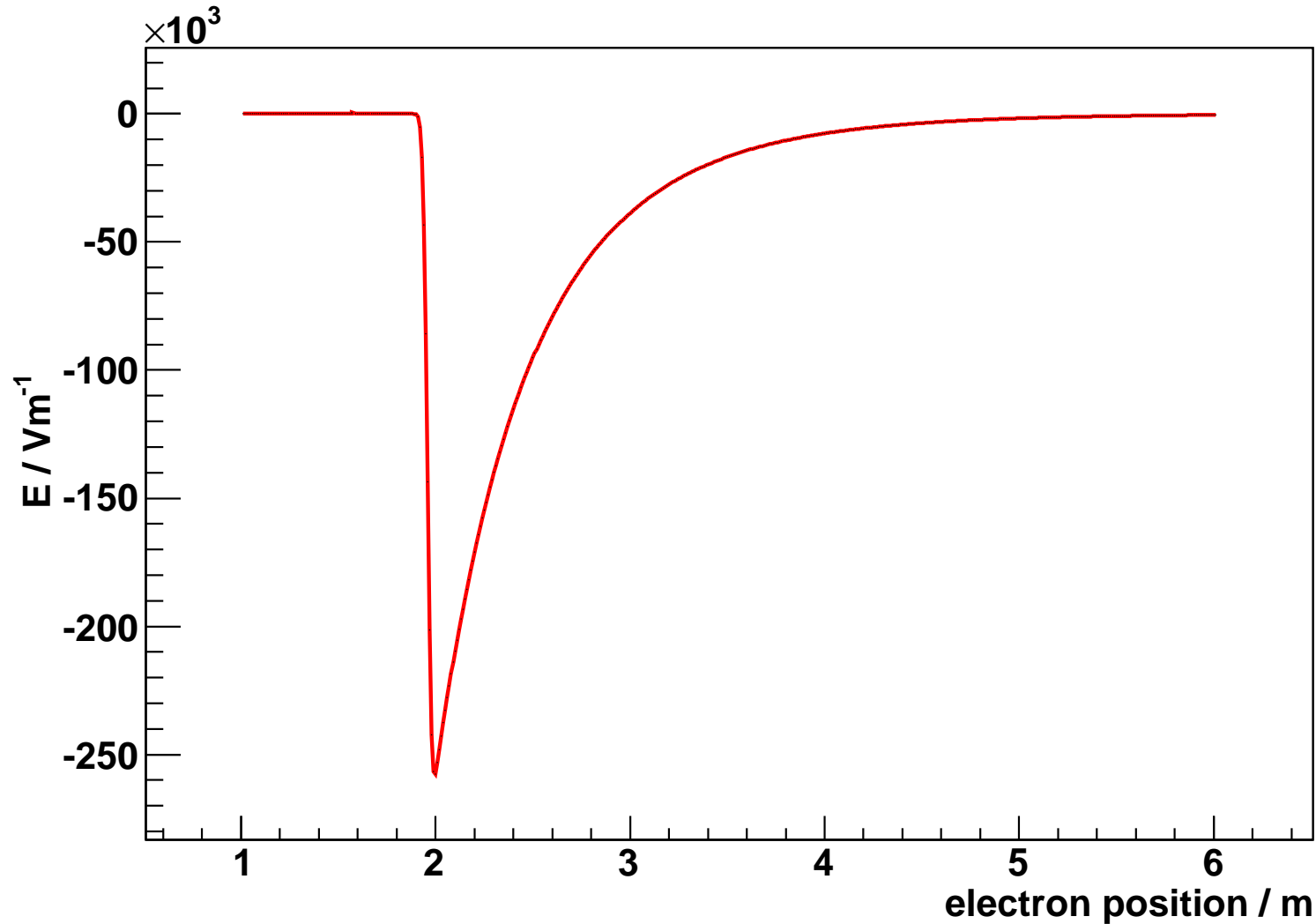
Simulated off-axis radial fields at 2.0 m



# Particle Tracking

$E_z$  seen by an 'on-axis' reference particle (20.8 MeV) coincident with the pulse at 2 m

Integrated field: -150 keV



# Conclusions

- Code has been optimised and CUDA (GPU) enabled
- Electric field calculation time  $\sim 300$  points per second
  - previously  $\sim 10$  seconds per point
- Benchmarking with experimental results is underway
  - Need to understand the overshoot pulse - could be important in tracking
- Energy could be modulated by several hundred keV - detectable
- Bunch Tracking is under way